

Stud-Mounted Silicon Rectifier Diodes, 15 A



DO-203AB (DO-5)

DESCRIPTION/FEATURES

- Low thermal impedance
- High case temperature
- Excellent reliability
- Maximum design flexibility
- Can be made to meet stringent military, aerospace and other high reliability requirements
- RoHS compliant



PRODUCT SUMMARY

$I_{F(AV)}$	15 A
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MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{F(AV)}$		15 ⁽¹⁾	A
	T_C	150 ⁽¹⁾	°C
I_{FSM}	50 Hz	239	A
	60 Hz	250 ⁽¹⁾	
I^2t	50 Hz	286	A ² s
	60 Hz	260	
$I^2\sqrt{t}$		3870	A ² √s
V_{RRM}	Range	50 to 600	V
T_J		- 65 to 175	°C

Note

⁽¹⁾ JEDEC registered values

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER		V_{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RM} , MAXIMUM DIRECT REVERSE VOLTAGE V
CATHODE TO CASE	ANODE TO CASE	$T_J = - 65\text{ °C TO }175\text{ °C}$	$T_J = - 65\text{ °C TO }175\text{ °C}$
1N3208	1N3208R	50 ⁽¹⁾	50 ⁽¹⁾
1N3209	1N3209R	100 ⁽¹⁾	100 ⁽¹⁾
1N3210	1N3210R	200 ⁽¹⁾	200 ⁽¹⁾
1N3211	1N3211R	300 ⁽¹⁾	300 ⁽¹⁾
1N3212	1N3212R	400 ⁽¹⁾	400 ⁽¹⁾
1N3213	1N3213R	500 ⁽¹⁾	500 ⁽¹⁾
1N3214	1N3214R	600 ⁽¹⁾	600 ⁽¹⁾

Note

⁽¹⁾ JEDEC registered values

FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average forward current at case temperature	I _{F(AV)}	180° sinusoidal conduction		15 ⁽¹⁾	A	
				150 ⁽¹⁾	°C	
Maximum peak one cycle non-repetitive surge current	I _{FSM}	Half cycle 50 Hz sine wave or 6 ms rectangular pulse	Following any rated load condition and with rated V _{RRM} applied	239	A	
		Half cycle 60 Hz sine wave or 5 ms rectangular pulse		250 ⁽¹⁾		
		Half cycle 50 Hz sine wave or 6 ms rectangular pulse	Following any rated load condition and with V _{RRM} applied following surge = 0	284		
		Half cycle 60 Hz sine wave or 5 ms rectangular pulse		297		
Maximum I ² t for fusing	I ² t	t = 10 ms	With rated V _{RRM} applied following surge, initial T _J = 150 °C	286	A ² s	
		t = 8.3 ms		260		
Maximum I ² t for individual device fusing		t = 10 ms	With V _{RRM} = 0 following surge, initial T _J = 150 °C	403		
		t = 8.3 ms		368		
Maximum I ² √t for individual device fusing	I ² √t ⁽²⁾	t = 0.1 to 10 ms, V _{RRM} = 0 following surge		3870	A ² √s	
Maximum forward voltage drop	V _{FM}	I _{F(AV)} = 15 A (47.1 A peak), T _C = 150 °C		1.5 ⁽¹⁾	V	
Maximum average reverse current	I _{R(AV)}	Maximum rated I _{F(AV)} and T _C = 150 °C		10 ⁽¹⁾	mA	

Notes

⁽¹⁾ JEDEC registered values

⁽²⁾ I^2t for time $t_x = I^2\sqrt{t} \times \sqrt{t_x}$

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating and storage temperature range		T _J , T _{Stg}		- 65 to 175 ⁽¹⁾	°C
Maximum internal thermal resistance, junction to case		R _{thJC}	DC operation	0.65	°C/W
Thermal resistance, case to sink		R _{thCS}	Mounting surface, smooth, flat and greased	0.25	
Mounting torque	minimum		Non-lubricated threads	2.3 (20)	N · m (lbf · in)
	maximum			3.5 (30)	
Weight				28.5	g
				1	oz.
Case style			JEDEC	DO-203AB (DO-5)	

Note

⁽¹⁾ JEDEC registered values



**DO-203AB (DO-5) for
1N1183, 1N3765, 1N1183A, 1N2128A, 1N3208 Series**

DIMENSIONS in millimeters (inches)

